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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











CONFIGURABLE MULTIPLE-FUNCTION GATE

Description

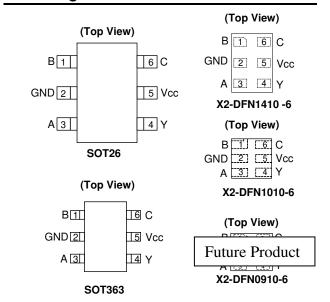
The 74AUP1G58 is a single, 3-input positive configurable multiple function gate with a standard push-pull output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions AND, OR, NAND, NOR, XOR, inverter or non-inverting buffer. All inputs can be connected to ground or Vcc as required.

The device is designed for operation with a power supply range of 0.8V to 3.6V.

The inputs are tolerant to 3.6V allowing this device to be used in a mixed voltage environment.

The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates but may respond differently due to the Schmitt action at the inputs.

Pin Assignments



Features

- Advanced Ultra Low-Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
- $I_C < 0.9 \mu A$
- Low Dynamic Power Consumption
- C_{PD} = 4.8pF Typical at 3.6V
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 950mV at $V_{CC} = 3.0V$.
- I_{OFF} Supports Partial-Power-Down Mode Operation
- ESD Protection per JESD 22
 - Exceeds 200-V Machine Model (A115)
 - Exceeds 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Standard SOT26 and SOT363 packages
- Leadless packages per JESD30E
 - DFN1410 denoted as X2-DFN1410-6
 - DFN1010 denoted as X2-DFN1010-6
 - DFN0910 denoted as X2-DFN0910-6
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

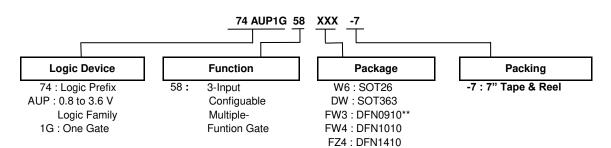
- Suited for Battery and Low Power Needs
- Voltage Level Shifting
- General Purpose Logic
- · Power Down Signal Isolation
- Wide array of products such as:
 - PCs, Networking, Notebooks, Netbooks, PDAs
 - Tablet Computers, E-readers
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set-Top Boxes
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



Device	Package Package		Package	7" Tape a	nd Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G58W6-7	W6	SOT26	3.0mm x 2.8mm x 1.2mm 0.95 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G58DW-7	DW	SOT363	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G58FW3-7**	FW3	X2-DFN0910-6	0.9mm x 1.0mm x 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7
74AUP1G58FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm lead pitch	5,000/Tape & Reel	-7
74AUP1G58FZ4-7	558FZ4-7 FZ4 X2-DFN1410-6 1.4mm x		1.4mm x 1.0mm x 0.4mm 0.5 mm lead pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

** The X2-DFN0910-6 is a future product.

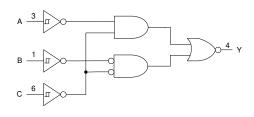
Pin Descriptions

Pin Name	Function
В	Data Input
GND	Ground
Α	Data Input
Υ	Data Output
V _{CC}	Supply Voltage
С	Data Input

Function Table

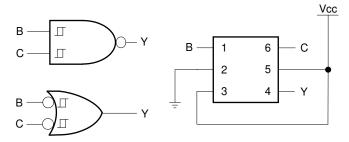
	Inputs		Output
С	В	Α	Υ
L	L	L	L
L	L	Η	Н
L	Н	L	L
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	L

Logic Diagram

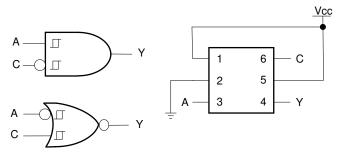




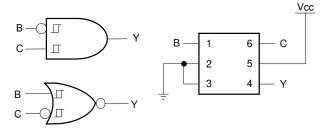
Logic Configurations



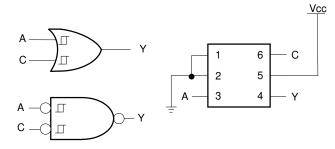
Configuration 1
2-Input NAND Gate
2-Input OR Gate with Both Inputs Inverted



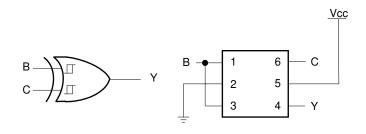
Configuration 3 2-Input AND Gate with C Input Inverted 2-Input NOR Gate with A Input Inverted



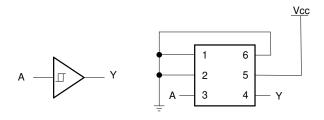
Configuration 2 2-Input AND Gate with B Input Inverted 2-Input NOR Gate with C input Inverted



Configuration 4
2-Input OR Gate
2-Input NAND Gate with Both Inputs Inverted



Configuration 5 2-Input XOR Gate



Configuration 6 Buffer

Function Selection Ta	able
Logic Function	Configuration
2-Input NAND	1
2-Input NAND with both inputs inverted	4
2-Input AND with inverted input	2,3
2-Input NOR with inverted input	2,3
2-Input OR	4
2-Input OR with both inputs inverted	1
2-Input XOR	5
1-Input Buffer	6



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	٧
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
lok	Output Clamp Current (V _O < 0)	-50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
lcc	Continuous Current through V _{CC}	50	mA
I _{GND}	Continuous Current through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 8)

Symbol		Parameter	Min	Max	Unit	
V_{CC}	Operating Voltage	-	0.8	3.6	V	
VI	Input Voltage		0	3.6	V	
Vo	Output Voltage	Active Mode Power Down Mode	0	V _{CC} 3.6	V	
		V _{CC} = 0.8 V	-	-20	μΑ	
	High land autout august	V _{CC} = 1.1 V	-	-1.1		
		V _{CC} = 1.4 V	-	-1.7		
Іон	High-level output current	V _{CC} = 1.65 V	-	-1.9	mA	
	Input Voltage Output Voltage High-level output current Low-level output current	V _{CC} = 2.3 V	-	-3.1		
		V _{CC} = 3.0 V	-	-4		
		V _{CC} = 0.8 V	-	20	μΑ	
		V _{CC} = 1.1 V	-	1.1		
	Low lovel output ourrent	V _{CC} = 1.4 V	-	1.7		
I _{OL}	Low-level output current	V _{CC} = 1.65 V	-	1.9	mA	
		V _{CC} = 2.3 V	-	3.1	<u> </u>	
		V _{CC} = 3.0 V	-	4		
T _A	Operating free-air temperature	-	-40	+125	°C	

Note: 8. Unused inputs should be held at Vcc or Ground.

Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
 Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics

			.,	T _A = +	+25°C	T _A =-40	to +85°C	
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit
		-	0.8V	0.3	0.65	0.3	0.7	
	Positive-Going	-	1.1V	0.53	0.9	0.53	0.9	
	_	-	1.4V	0.74	1.11	0.74	1.11	V
V_{T+}	Input Threshold	-	1.65V	0.91	1.29	0.91	1.29] v
	Voltage	-	2.3V	1.37	1.77	1.37	1.77	
		-	3.0V	1.88	2.29	1.88	2.29	
		-	0.8V	0.1	0.6	0.1	0.6	
	Negative-Going	-	1.1V	0.26	0.65	0.26	0.65	
V_{T-}	Input Threshold	-	1.4V	0.39	0.75	0.39	0.75	V
V _T .	· ·	-	1.65V	0.47	0.84	0.47	0.84	_
	Voltage	-	2.3V	0.69	1.04	0.69	1.04	
		-	3.0V	0.88	1.24	0.88	1.24	
		-	0.8V	0.07	0.5	0.07	0.5	
		-	1.1V	0.08	0.46	0.08	0.46	
ΔV_T	Hysteresis	-	1.4V	0.18	0.56	0.18	0.56	V
77 V	$(V_{T+} - V_{T-})$	-	1.65V	0.27	0.66	0.27	0.66	
		-	2.3V	0.53	0.92	0.53	0.92	
		-	3.0V	0.79	1.31	0.79	1.31	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.1	-	V _{CC} - 0.1	-	
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.75 x V _{CC}	-	$0.7 \times V_{CC}$	-	
,, l		$I_{OH} = -1.7 \text{mA}$	1.4V	1.11	-	1.03	-	
	High-Level Output Voltage	$I_{OH} = -1.9 \text{mA}$	1.65V	1.32	-	1.3	-	.,
V_{OH}		$I_{OH} = -2.3 \text{mA}$	0.01/	2.05	-	1.97	-	V
		I _{OH} = -3.1mA	2.3V	1.9	-	1.85	-	1
		I _{OH} = -2.7mA		2.72	-	2.67	-	1
		$I_{OH} = -4mA$	3V	2.6	-	2.55	-	
		$I_{OL} = 20\mu A$	0.8V to 3.6V		0.1	-	0.1	
		$I_{OL} = 20\mu$ K $I_{OL} = 1.1 \text{mA}$	1.1V	-	0.3 x V _{CC}	_	0.3 x V _{CC}	1
		$I_{OL} = 1.7 \text{mA}$ $I_{OL} = 1.7 \text{mA}$	1.4V	-	0.3 x V _{CC}	_	0.3 x V _{CC}	1
								1
V_{OL}	Low-Level Input	I _{OL} = 1.9mA	1.65 V	-	0.31	-	0.35	V
	Voltage	I _{OL} = 2.3mA	2.3V	-	0.31		0.33	_
		$I_{OL} = 3.1 \text{mA}$		-	0.44	-	0.45	
		$I_{OL} = 2.7 \text{mA}$	3V	-	0.31	-	0.33	_
		$I_{OL} = 4 \text{ mA}$		-	0.44	-	0.45	
l _l	Input Current	A or B Input V _I =GND to 3.6 V	0V to 3.6V	-	± 0.1	-	± 0.5	μΑ
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0$ V to 3.6V	0	-	± 0.2	-	± 0.6	μA
ΔI_{OFF}	Delta Power Down Leakage Current	V ₁ or V _O = 0V to 3.6V	0V to 0.2 V	-	± 0.2	-	± 0.6	μΑ
I _{CC}	Supply Current	$V_1 = GND \text{ or } V_{CC}$ $I_0=0$	0.8V to 3.6V	-	0.5	-	0.9	μΑ
ΔI_{CC}	Additional Supply Current	One input at V _{CC} – 0.6 V Other inputs at V _{CC} or GND	3.3V	-	40	-	50	μА



Electrical Characteristics (continued)

		o . i:::	.,	T _A =-40 1	o +125°C	
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Unit
		-	0.8V	0.3	0.7	
	Positive-Going	-	1.1V	0.53	0.92	
	Input	=	1.4V	0.74	1.13	v
$V_{T_{+}}$	Threshold	-	1.65V	0.91	1.31	V
	Voltage	-	2.3V	1.37	1.8	
	Ŭ	-	3.0V	1.88	2.32	
		=	0.8V	0.1	0.6	
	Negative-	-	1.1V	0.26	0.65	
\/	Going Input	-	1.4V	0.39	0.75	V
V_{T-}	Threshold	-	1.65V	0.47	0.84	V
	Voltage	-	2.3V	0.69	1.04	
	ŭ	-	3.0V	0.88	1.24	
		-	0.8V	0.07	0.5	
		-	1.1V	0.08	0.46	
ΔV_T	Hysteresis	-	1.4V	0.18	0.56	V
ΔVT	$(V_{T+} - V_{T-})$	-	1.65V	0.27	0.66	, v
		-	2.3V	0.53	0.92	
		-	3.0V	0.79	1.31	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	$V_{CC} - 0.11$	-	
		I _{OH} = -1.1mA	1.1V	0.6 x V _{CC}	-	
		I _{OH} = -1.7mA	1.4V	0.93	-	
	High-Level	I _{OH} = -1.9mA	1.65V	1.17	-	
V_{OH}	Output	I _{OH} = -2.3mA		1.77	-	V
	Voltage	I _{OH} = -3.1mA	2.3V	1.67	-	
		$I_{OH} = -2.7 \text{mA}$		2.40	-	
		$I_{OH} = -4mA$	3V	2.30	_	
		$I_{OL} = 20\mu A$	0.8V to 3.6V	-	0.11	
		$I_{OL} = 1.1 \text{mA}$	1.1V	_	0.33 x V _{CC}	
		$I_{OL} = 1.7 \text{mA}$	1.4V	_	0.41	
	l and land	$I_{OL} = 1.9 \text{mA}$	1.65 V	_	0.39	
V_{OL}	Low-Level Input Voltage		1.05 V		0.36	V
	input voltage	I _{OL} = 2.3mA	2.3V	_		
		I _{OL} = 3.1mA		-	0.50	
		$I_{OL} = 2.7 \text{mA}$	3V		0.36	
		I _{OL} = 4mA		-	0.50	
I_1	Input Current	A or B Input $V_1 = GND$ to 3.6 V	0V to 3.6V	-	± 0.75	μΑ
I _{OFF}	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0	-	± 1.0	μΑ
ΔI_{OFF}	Delta Power Down Leakage Current	V ₁ or V _O = 0V to 3.6V	0V to 0.2 V	-	± 2.5	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}$ $I_O=0$	0.8V to 3.6V	-	1.4	μΑ
ΔI_{CC}	Additional Supply Current	One input at V _{CC} – 0.6 V Other inputs at V _{CC} or GND	3.3V	-	75	μΑ



Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур.	Max	Unit
		SOT26		-	166	1	
θιΔ		SOT363		-	371	-	
	Thermal Resistance Junction-	X2-DFN0910-6	(Note 9)	-	450	-	°C/W
	to-Ambient	X2-DFN1010-6	, ,	-	445	-	
		X2-DFN1410-6		-	430	-	
		SOT26		-	46	-	
		SOT363		-	143	-	
θ_{JC}	Thermal Resistance Junction-	X2-DFN0910-6	(Note 9)	-	255	-	°C/W
00	to-Case	X2-DFN1010-6		-	250	-	
		X2-DFN1410-6			190	-	

Note: 9. Test condition for each of the 8 package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Operating Characteristics (@T_A = +25°C, unless otherwise specified.)

Р	arameter	Test Conditions	Vcc	ТҮР	Unit
	Power f = 1MHz Dissipation		0.8 V 1.2V ± 0.1V	4	
0		f = 1MHz	1.5V ± 0.1V	4	
C_pd	Capacitance	No Load	1.8V ± 0.15V	4	pF
	Capacitance		2.5V ± 0.2V	4.4	
			$3.3 \pm 0.3 V$	4.8	
Cı	Input Capacitance	$V_i = V_{CC}$ or GND	0 V or 3.3V	1.1	pF
Co	Output Capacitance	V ₀ = V _{CC} or GND	0 V	2.0	pF

Switching Characteristics

C_L=5pF, See Figure 1

D	From	то	V			to +85°C	85°C $T_A = -40$ °C to +125°C				
Parameter	Input	OUTPUT	V _{cc}	Min	TYP	Max	Min Max	Min	Max	Unit	
			0.8 V	-	28	-	-	-	-	-	
	Α,	A, B, or	1.2 V ± 0.1 V	2.8	7.5	14.7	2.3	14.9	2.3	15.2	
+ .	В,		1.5 V ± 0.1 V	2.1	4.8	7.7	1.6	8.3	1.6	8.6	ns
t _{pd}			1.8 V ± 0.15 V	1.5	4	6.3	1	7	1	7.3	115
	С		2.5 V ± 0.2 V	1.1	3.2	4.6	0.6	5.2	0.6	5.4	
			3.3 V ± 0.3 V	1	2.9	4	0.5	4.2	0.5	4.4	



Switching Characteristics (continued)

 $C_L=10pF$, See Figure 1

Parameter	From	то	v	7	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C	
Farameter	Input	OUTPUT	V _{CC}	Min	TYP	TYP Max	Min	Max	Min	Max	Unit
Α.			0.8 V	-	32	-	-	-	-	-	
	Α,	A, B, or C	1.2 V ± 0.1 V	3.2	8.4	16.5	2.7	17	2.7	17.3	
	В,		1.5 V ± 0.1 V	2	5.4	8.8	1.5	9.5	1.5	9.8	no
t _{pd}	or		1.8 V ± 0.15 V	1.1	4.5	7.2	0.6	8	0.6	8.3	ns
	С		2.5 V ± 0.2 V	1	3.8	5.3	0.5	5.9	0.5	6.2	
			3.3 V ± 0.3 V	1	3.5	4.7	0.5	4.9	0.5	5.1	

C_L=15pF, See Figure 1

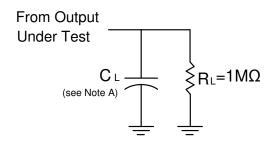
PFrom		то	то	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C to +125°C		11:4		
Parameter	Parameter Input OUTPUT	Vcc	Min	TYP	Max	Min	Max	Min	Max	Unit		
				0.8 V	-	36	-	-	-	-	-	
	Α,	A, B, or C	1.2 V ± 0.1 V	3.6	9.5	18.4	3.3	19.8	3.3	20		
			1.5 V ± 0.1 V	2.9	5.9	11.1	2.4	12	2.4	11		
t _{pd}	or		1.8 V ± 0.15 V	2.2	5	9	1.7	9.9	1.7	9.2	ns	
	С		2.5 V ± 0.2 V	1.7	4.2	6.7	1.2	7.5	1.2	6.9		
			3.3 V ± 0.3 V	1.4	3.9	5.9	0.9	6.3	0.9	5.8		

C_I =30pF, See Figure 1

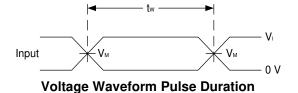
P From		то	то	$T_A = +25^{\circ}C$		$T_A = -40$ °C to 85°C		T _A = -40°C to +125°C			
Parameter	Input OUTPUT	V _{CC}	Min	ТҮР	Max	Min	Max	Min	Max	Unit	
	Α,	0.8 V	-	46	-	-	-	-	-		
			1.2 V ± 0.1 V	4.5	12	23.7	4.1	25	4.1	25.5	
	В,	Y	1.5 V ± 0.1 V	3.8	7.5	13.9	3.5	15.4	3.5	14.1	
t _{pd}	or		1.8 V ± 0.15 V	3.2	6.3	11.4	2.7	12.8	2.7	11.9	ns
	С	2.5 V ± 0.2 V	2.5	5.3	8.6	2	9.6	2	8.9		
			3.3 V ± 0.3 V	2.1	5	7.5	1.6	8.1	1.6	7.4	

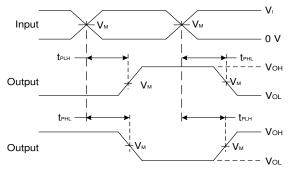


Parameter Measurement Information



V _{CC}	Inputs		V _M	CL
	VI	t _r /t _f		_
0.8 V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30 pF
1.2V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30 pF
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30 pF
1.8V±0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30 pF
2.5V±0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30 pF
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30 pF





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{PD}.



Marking Information

(1) SOT26, SOT363

5 6 4 XX Y W X 1 2 3

XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week

X: A~Z: Internal Code

Part Number	Package	Identification Code
74AUP1G58W6	SOT26	AX
74AUP1G58DW	SOT363	BW

(2) X2-DFN0910-6, X2-DFN1010-6, X2-DFN1410-6

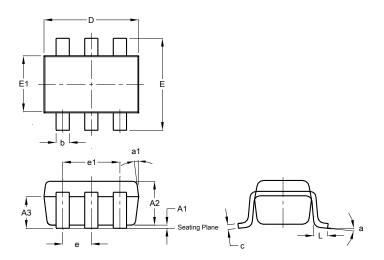
(Top View)

XX: I dentification Code
Y: Year: 0~9
W: Week: A~Z: 1~26 week;
a~z: 27~52 week; z represents
52 and 53 week
X: A~Z: Internal code

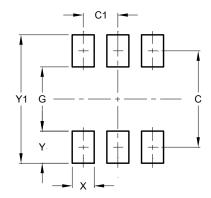
Part Number	Package	Identification Code
74AUP1G58FW3	X2-DFN0910-6	AX
74AUP1G58FW4	X2-DFN1010-6	BW
74AUP1G58FZ4	X2-DFN1410-6	NS



SOT26 Package Outline Dimensions and Suggested Pad Layout



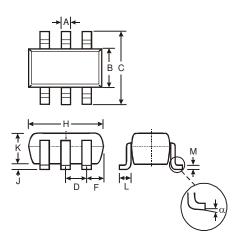
	SC	OT26	
Dim	Min	Max	Тур
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
С	0.10	0.20	0.15
D	2.90	3.10	3.00
е	-	1	0.95
e1	-	ı	1.90
Е	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
а	-	-	8°
a1	-	-	7°
All	Dimen	sions	in mm



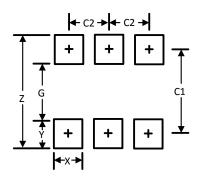
Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



SOT363 Package Outline Dimensions and Suggested Pad Layout



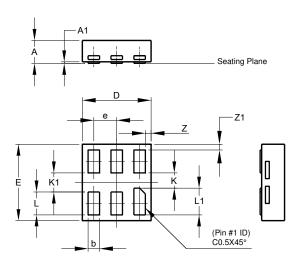
	SOT363						
Dim	Min	Max	Тур				
Α	0.10	0.30	0.25				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D		0.65 Ty	р				
F	0.40	0.45	0.425				
Н	1.80	2.20	2.15				
7	0	0.10	0.05				
K	0.90	1.00	1.00				
L	0.25	0.40	0.30				
М	0.10	0.22	0.11				
α	0°	8°	-				
All	Dimen	sions i	n mm				



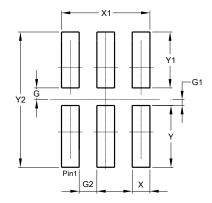
Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65



X2-DFN0910-6 Package Outline Dimensions and Suggested Pad Layout



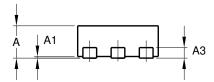
	X2-DFN0910-6						
Dim	Min	Max	Тур				
Α	1	0.35	0.30				
A1	0	0.03	0.02				
b	0.10	0.20	0.15				
D	0.85	0.95	0.90				
Ε	0.95	1.05	1.00				
е	1	-	0.30				
K	0.20	-	-				
K1	0.25	-	-				
L	0.25	0.35	0.30				
L1	0.30	0.40	0.35				
Z	-	-	0.075				
Z 1	-	-	0.075				
All	Dimensi	ons in	mm				

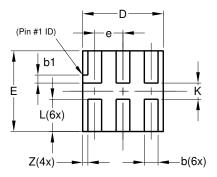


Dimensions	Value (in mm)
G	0.100
G1	0.050
G2	0.150
Х	0.150
X1	0.750
Υ	0.525
Y1	0.475
Y2	1.150

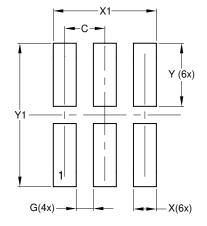


X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





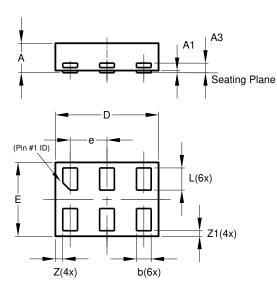
	X2-DFN1010-6						
Dim	Min	Max	Тур				
Α		0.40	0.39				
A1	0.00	0.05	0.02				
A3			0.13				
b	0.14	0.20	0.17				
b1	0.05	0.15	0.10				
D	0.95	1.05	1.00				
Е	0.95	1.05	1.00				
е	_	_	0.35				
L	0.35	0.45	0.40				
K	0.15		_				
Z			0.065				
All [Dimens	ions in	mm				



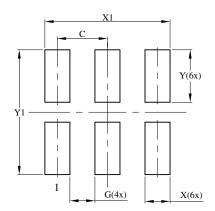
Dimensions	Value (in mm)
С	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250



X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A 1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е	_	_	0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z 1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Υ	0.525
Y1	1.250



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